

DSA12T

Diffused Junction Type Silicon Diode

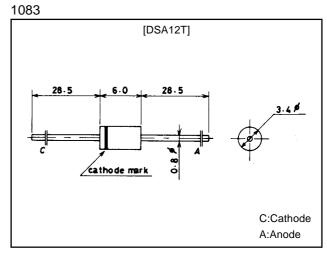
1.2A Power Rectifier

Features

- · Plastic molded structure.
- \cdot Peak Reverse Voltage : V_{RM}=100 to 1000V
- \cdot Average rectified current : I_O=1.2A.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

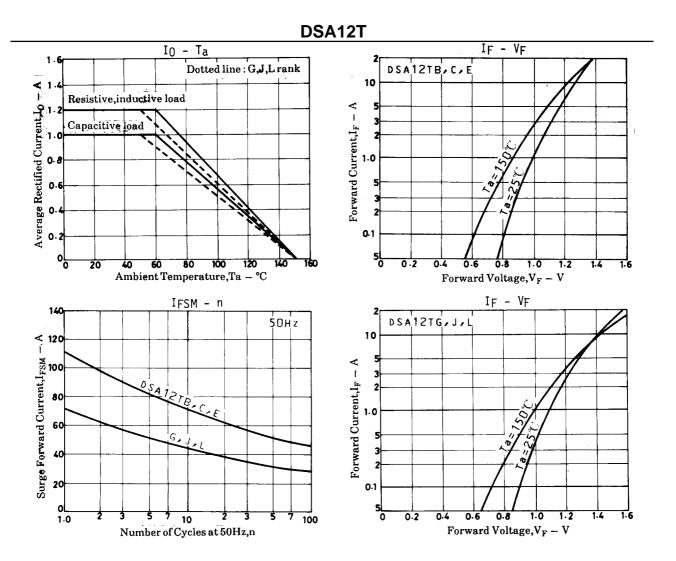
| Parameter | Symbol | Conditions | DSA12TB | DSA12TC | DSA12TE | Unit |
|---------------------------|-----------------|-------------------------|---------------|---------------|-------------|------|
| Peak Reverse Voltage | V _{RM} | | 100 | 200 | 400 | V |
| Average Rectified Current | IO | Ta=60°C | \rightarrow | \rightarrow | 1.2 | А |
| Surge Forward Current | IFSM | 50Hz sine wave, 1 cycle | \rightarrow | \rightarrow | 110 | A |
| Junction Temperature | Tj | | \rightarrow | \rightarrow | 150 | °C |
| Sotrage Temperature | Tstg | | \rightarrow | \rightarrow | -40 to +150 | °C |

| Parameter | Symbol | Conditions | DSA12TG | DSA12TJ | DSA12TL | Unit |
|---------------------------|-----------------|-------------------------|---------------|---------------|-------------|------|
| Peak Reverse Voltage | V _{RM} | | 600 | 800 | 1000 | V |
| Average Rectified Current | IO | Ta=50°C | \rightarrow | \rightarrow | 1.2 | A |
| Surge Forward Current | IFSM | 50Hz sine wave, 1 cycle | \rightarrow | \rightarrow | 70 | A |
| Junction Temperature | Tj | | \rightarrow | \rightarrow | 150 | °C |
| Storage Temperature | Tstg | | \rightarrow | \rightarrow | -40 to +150 | °C |

Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|-----------------|----------------|---|---------|-----|-----|-------|
| | | | min | typ | max | Offic |
| Forward Voltage | ٧ _F | I _F =1.2A(B, C, E) | | | 1.0 | V |
| | | I _F =1.2A(G, J, L) | | | 1.1 | V |
| Reverse Current | ۱ _R | V _R :At each V _{RM} | | | 10 | μΑ |

SANYO Electric Co., Ltd. Semiconductor Bussiness Headquarters TOKYO OFFICE, Tokyo Bldg., 1-10, Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN



■ No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.

Anyone purchasing any products described or contained herein for an above-mentioned use shall:

- Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:
- ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of May, 1998. Specifications and information herein are subject to change without notice.